



74LVC1G17

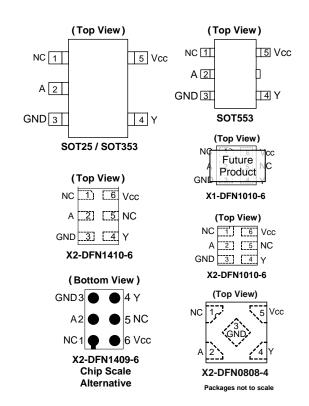
SINGLE SCHMITT-TRIGGER BUFFER

Description

The 74LVC1G17 is a single 1-input Schmitt-trigger buffer with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using $l_{\rm OFF}$. The $l_{\rm OFF}$ circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

$$Y = A$$

Pin Assignments



Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- · CMOS low power consumption
- I_{OFF} Supports Partial-Power-Down Mode Operation
- · Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2,000-V Human Body Model (A114)
 - Latch-Up Exceeds 100mA per JESD 78, Class I
- Range of Package Options
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

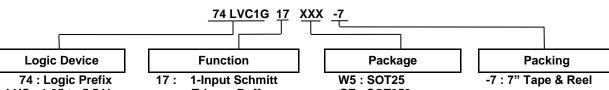
- · Voltage Level Shifting
- · General Purpose Logic
- · Power Down Signal Isolation
- · Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and < 1000 ppm antimony compounds.



Ordering Information



LVC: 1.65 to 5.5 V **Logic Family** 1G: One Gate

Trigger Buffer

SE: SOT353 Z: SOT553 FS3: X2-DFN0808-4 FW5: X1-DFN1010-6 FW4:X2-DFN1010-6

FX4: X2- DFN1409-6 FZ4: X2- DFN1410-6

Devilee	Package	Package	Package	7" Tape and Reel			
Device	Code	(Notes 4, 5)	Size	Quantity	Part Number Suffix		
74LVC1G17W5-7	W5	SOT25	3.0mm X 2.8mm X 1.2mm 0.95 mm lead pitch	3,000/Tape & Reel	-7		
74LVC1G17SE-7	SE	SOT353	2.0mm X 2.0mm X 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7		
74LVC1G17Z-7	Z	SOT553	1.1.6mm X 1.6 mm X 0.62mm 0.5 mm lead pitch	4,000/Tape & Reel	-7		
74LVC1G17FS3-7	FS3	X2-DFN0808-4	0.9mm X 0.9 mm X 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7		
74LVC1G17FW5-7 (Future Product)	FW5	X1-DFN1010-6 (Future Product)	1.0mm X 1.0mm X 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7		
74LVC1G17FW4-7	FW4	X2-DFN1010-6	1.0mm X 1.0mm X 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7		
74LVC1G17FX4-7	FX4	X2-DFN1409-6 (Chip Scale Alternative)	1.4mm X 0.9mm X 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7		
74LVC1G17FZ4-7	FZ4	X2-DFN1410-6	1.4mm X 1.0mm X 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7		

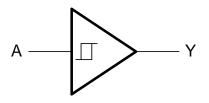
Notes:

- 4. Pad layout as shown on Diodes' suggested pad layout, which can be found on our website at http://www.diodes.com/package-outlines.html.
- 5. The taping orientation is located on our website at https://www.diodes.com/assets/Diodes-Packaging/ap02007.pdf.

Pin Descriptions

Pin Name	Description
Α	Data Input
GND	Ground
Υ	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inputs	Output
Α	Υ
Н	Н
L	L



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High Impedance or I _{OFF} State	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	-50	mA
lok	Output Clamp Current	-50	mA
Ιο	Continuous Output Current	±50	mA
I _{CC} , I _{GND}	Continuous Current through V _{CC} or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol		Parameter	Min	Max	Unit
\ /	On and the sell-like sec	Operating	1.65	5.5	V
V _{CC}	Operating Voltage	Data retention only	1.5	_	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 1.65V	_	-4	
		V _{CC} = 2.3V	_	-8	
	I Falls I arred Ordered arressed	V _{CC} = 2.7V	_	-12	
I _{OH}	High-Level Output current	V	_	-16	mA
		$V_{CC} = 3V$	_	-24	
		V _{CC} = 4.5V	_	-32	
		V _{CC} = 1.65V	_	4	
		V _{CC} = 2.3V	_	8	
	Lave Lave Control comment	V _{CC} = 2.7V	_	12	
l _{OL}	Low-Level Output current	V	_	16	mA
		$V_{CC} = 3V$	_	24	
		V _{CC} = 4.5V	_	32	
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at VCC or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{7.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range..



Electrical Characteristics $T_A = -40^{\circ}C$ to $+85^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
		_	1.65V	0.70	_	1.20	_
		_	2.3V	1.11	_	1.60	_
V_{T+}		_	3V	1.50	_	2.00	_
	Threshold voltage	_	4.5V	2.16	_	2.74	_
		_	5.5V	2.61	_	3.33	_
	(V _{T+} - V _{T-})	_	1.65V	0.30	_	0.72	_
		_	2.3V	0.58	_	1.00	_
V _T -		_	3V	0.80	_	1.30	_
	Threshold voltage	_	4.5V	1.21	_	1.95	_
	Positive-going Input Threshold Voltage Negative-going Input Threshold Voltage Hysteresis (V _{T+} - V _{T-}) High Level Output Voltage Low-Level Output Voltage	_	5.5V	1.45	_	2.35	_
		_	1.65V	0.30	_	0.62	_
		_	2.3V	0.40	_	0.80	_
ΔV_T		_	3V	0.35	_	1.00	_
	(VT+ - VT-)	_	4.5V	0.55	_	1.10	_
		_	5.5V	0.60	_	1.20	_
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} - 0.1	_	_	
		I _{OH} = -4mA	1.65V	1.2	_	_	
		I _{OH} = -8mA	2.3V	1.9	_	_	
Voн	High Level Output Voltage	I _{OH} = -12mA	2.7V	2.2	_	_	V
		I _{OH} = -16mA	0)/	2.4	_	_	
		I _{OH} = -24mA	3V	2.3	_	_	
	VoH High Level Output Voltage	I _{OH} = -32mA	4.5V	3.8	_	_	
		I _{OL} = 100μA	1.65V to 5.5V	_	_	0.1	
		$I_{OL} = 4mA$	1.65V	_	_	0.45	
		$I_{OL} = 8mA$	2.3V	_	_	0.3	
V _{OL}	Low-Level Output Voltage	I _{OL} = 12mA	2.7V	_	_	0.4	V
		I _{OL} = 16mA	2)/	_	_	0.4	
		I _{OL} = 24mA	3V	_	_	0.55	
		$I_{OL} = 32mA$	4.5V	_	_	— 0.55	
II	Input Current	V _I = 5.5 V or GND	0 to 5.5V	_	_	± 5	μA
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 5.5V$	0	_	_	± 10	μA
Icc	Supply Current	$V_I = 5.5V$ of GND $I_O = 0$	1.65V to 5.5V	_	_	10	μA
Δlcc	Additional Supply Current	Input at V _{CC} –0.6V	3V to 5.5V			500	μA



Electrical Characteristics (@ $T_A = -40$ °C to +125°C. All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
		_	1.65V	0.70	_	1.20	_
		_	2.3V	1.11	_	1.60	_
V_{T+}	• .	_	3 V	1.50	_	2.00	_
	Threshold voltage	_	4.5V	2.16	_	2.74	_
		_	5.5V	2.61	_	3.33	_
		_	1.65V	0.30	_	0.75	_
		_	2.3V	0.58		1.03	_
V_{T-}		_	3V	0.80		1.33	_
	i nresnoid voitage	_	4.5V	1.21		1.95	_
	Negative-Going Input Threshold Voltage VT Hysteresis (VT+ - VT-) OH High Level Output Voltage	_	5.5V	1.45		2.35	_
		_	1.65V	0.30		0.62	
		_	2.3V	0.37		0.80	
ΔV_T	I -	_	3V	0.32		1.00	1
	(V _{T+} - V _{T-})	_	4.5V	0.50		1.20	
		_	5.5V	0.55		1.40	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} – 0.1		_	
		I _{OH} = -4mA	1.65V	0.95		_	
		I _{OH} = -8mA	2.3V	1.7		_	
VoH	High Level Output Voltage	I _{OH} = -12mA	2.7V	1.9		_	V
		I _{OH} = -16mA		2.2		_	
		I _{OH} = -24mA	3V	2.0		_	
		I _{OH} = -32mA	4.5V	3.4		_	
		I _{OL} = 100μA	1.65V to 5.5V	_		0.1	
		I _{OL} = 4mA	1.65V	_		0.7	
		I _{OL} = 8mA	2.3V	_		0.45	
V_{OL}	High-Level Input Voltage	I _{OL} = 12mA	2.7V	_		0.6	V
		I _{OL} = 16mA		_		0.6	
		I _{OL} = 24mA	3V	_		0.8	
		I _{OL} = 32mA	4.5V	_		0.8	
II	Input Current	V _I = 5.5 V or GND	0 to 5.5V	_		± 100	μA
l _{OFF}	•		0	_	_	± 200	μA
Icc	Supply Current	V _I = 5.5V of GND I _O = 0	1.65V to 5.5V	_		200	μA
Δlcc	Additional Supply Current	Input at V _{CC} – 0.6 V	3V to 5.5V	_	_	5,000	μΑ



Package Characteristics (All typical values are at V_{CC} = 3.3V, T_A = +25°C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
		SOT25		_	204	_	
		SOT353		_	371	_	
		SOT553		_	231	_	
	Thermal Resistance	X2-DFN0808-4	(NI=1= 0)	_	400	_	0000
θ_{JA}	Junction-to-Ambient	X1-DFN1010-6	(Note 9)	_	435	_	°C/W
		X2-DFN1010-6		_	445	_	
		X2-DFN1409-6		_	470	_	
		X2-DFN1410-6		_	460	_	
		SOT25		_	52	_	°C/W
		SOT353		_	143	_	
		SOT553		_	105	_	
	Thermal Resistance	X2-DFN0808-4	(1) (2)	_	225	_	
θЈС	Junction-to-Case	X1-DFN1010-6	(Note 9)	_	250	_	
		X2-DFN1010-6		_	250	_	
		X2-DFN1409-6		_	275	_	
		X2-DFN1410-6		_	265	_	

Note: 9. Test condition for each of the 8 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

 $T_A = -40$ °C to +85°C, $C_L = 15$ pF as noted (See Figure 1)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	Α	Υ	1.0	9.9	0.7	5.5	0.7	4.6	0.7	4.4	ns

 T_A = -40°C to +85°C, C_L = 30 or 50pF as noted (See Figure 2)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	А	Υ	1.0	11	0.7	6.5	0.7	5.5	0.7	5	ns

 $T_A = -40$ °C to +125°C, $C_L = 15$ pF as noted (See Figure 1)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	Α	Υ	1.0	12.5	0.7	7.5	0.7	6.5	0.7	5.5	ns

 $T_A = -40$ °C to +125°C, $C_L = 30$ or 50pF as noted (See Figure 2)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	А	Υ	1.0	14.0	0.7	8.5	0.7	7.0	0.7	6.5	ns

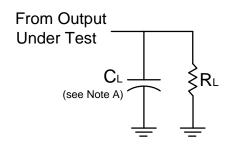


Operating Characteristics

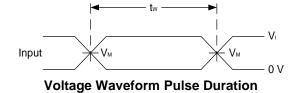
 $T_A = +25$ °C

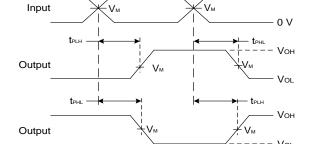
	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{PD}	Power Dissipation Capacitance	f = 10 MHz	20	22	23	25	pF

Parameter Measurement Information



V	Inputs		V	•	
V _{CC}	VI	t _R /t _F	V _M	CL	R_L
1.8V±0.15V	Vcc	≤2ns	V _{CC} /2	15pF	1ΜΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1ΜΩ





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

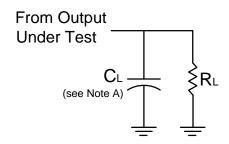
Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

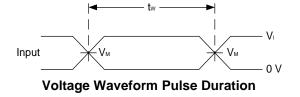
- B. All pulses are supplied at pulse repetition rate ≤ 10MHz.
 C. Inputs are measured separately one transition per measurement.
- D. tpLH and tpHL are the same as tpD.

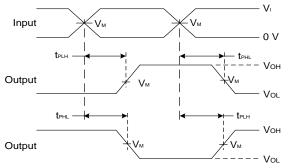


Parameter Measurement Information (Continued)



V	In	puts	V	•	Б	
V _{CC}	VI	t _R /t _F	V _M	C∟	R_L	
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1kΩ	
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω	





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 2. Load Circuit and Voltage Waveforms

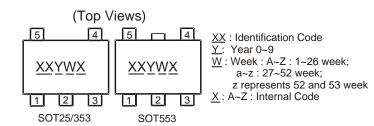
Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



Marking Information

(1) SOT25, SOT353 and SOT553



Part Number	Package	Identification Code
74LVC1G17W5-7	SOT25	UR
74LVC1G17SE-7	SOT353	UR
74LVC1G17Z-7	SOT553	UR

(2) DFN packages





 $\begin{array}{l} \underline{XX}: \mbox{Identification Code} \\ \underline{Y}: \mbox{ Year 0~9} \\ \underline{W}: \mbox{Week}: \mbox{A~Z}: \mbox{1~26 week}; \end{array}$ a~z: 27~52 week;

z represents 52 and 53 week

 \underline{X} : A~Z: Internal Code

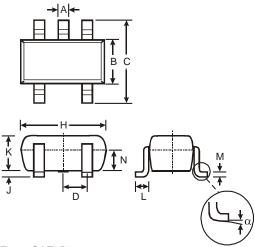
Part Number	Package	Identification Code
74LVC1G17FS3-7	X2-DFN0808-4	WR
74LVC1G17FW5-7	X1-DFN1010-6	V9
74LVC1G17FW4-7	X2-DFN1010-6	UR
74LVC1G17FX4-7	X2-DFN1409-6	MH
74LVC1G17FZ4-7	X2-DFN1410-6	UR



Package Outline Dimensions

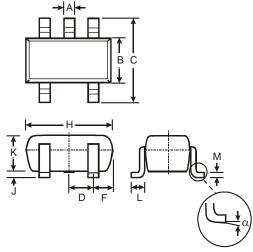
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SOT25



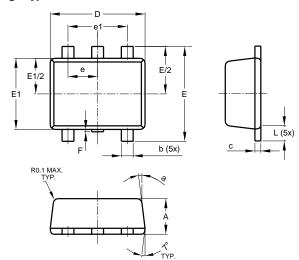
	SOT25					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	_		0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
M	0.10	0.20	0.15			
N	0.70	0.80	0.75			
α	0°	8°	_			
All D	imensi	ons in	mm			

(2) Package Type: SOT353



	SOT353					
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 Typ					
F	0.40	0.45				
Н	1.80	2.20				
J	0	0.10				
K	0.90	1.00				
L	0.25	0.40				
M	0.10	0.22				
α	0°	8°				
All Di	mensions	in mm				

(3) Package Type: SOT553



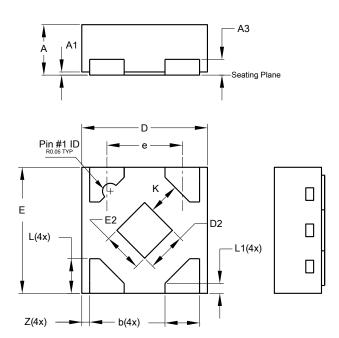
	SOT553					
Dim	Min	Max	Тур			
Α	0.55	0.62	0.60			
b	0.15	0.30	0.20			
С	0.10	0.18	0.15			
D	1.50	1.70	1.60			
Е	1.55	1.70	1.60			
E1	1.10	1.25	1.20			
е	0	.50 BS0				
e1	1	.00 BS0				
F	0.00	0.10	_			
L	0.10	0.30	0.20			
а	6°	8°	7°			
All	Dimens	ions in	mm			



Package Outline Dimensions (Continued)

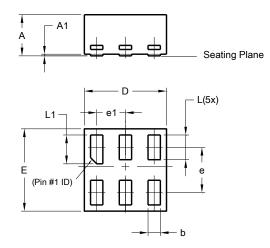
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type X2-DFN0808-4



	X2-DFN0808-4					
Dim	Min	Max	Тур			
Α	0.25	0.35	0.30			
A1	0	0.04	0.02			
A3		-	0.13			
b	0.17	0.27	0.22			
D	0.75	0.85	0.80			
D2	0.15	0.35	0.25			
E	0.75	0.85	0.80			
E2	0.15	0.35	0.25			
е	=	-	0.48			
K	0.20	-	-			
L	0.17	0.27	0.22			
L1	0.02	0.12	0.07			
Z	-	-	0.05			
A	II Dimens	ions in r	nm			

(5) Package Type: X1-DFN1010-6

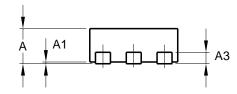


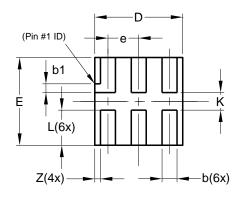
X1-DFN1010-6					
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е		0.55 B	SC		
e1	(0.35 B	SC		
L	0.27	0.35	0.30		
L1	0.32	0.40	0.35		
All Dimensions in mm					



Package Outline Dimensions (Cont.)

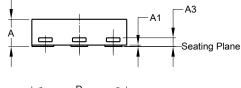
(6) Package Type X2-DFN1010-6

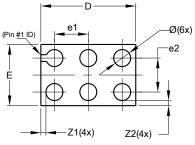




X2-DFN1010-6					
Dim	Min	Max	Тур		
Α	_	0.40	0.39		
A1	0.00	0.05	0.02		
A3	_		0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
е	_	_	0.35		
L	0.35	0.45	0.40		
K	0.15				
Ζ	_		0.065		
All	Dimens	ions in	mm		

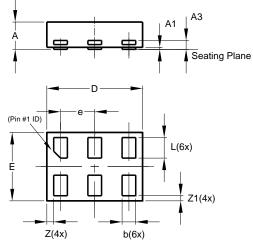
(7) Package Type: X2-DFN1409-6 6 (Chip Scale Alternative)





X2-DFN1409-6					
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A 1	0	0.05	0.02		
A3	-	-	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
Z 1	-	-	0.075		
Z 2	-	-	0.075		
All	Dimens	ions in	mm		

(8) Package Type: X2-DFN1410-6



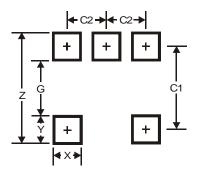
X2-DFN1410-6			
Dim	Min	Max	Тур
Α	_	0.40	0.39
A 1	0.00	0.05	0.02
А3			0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
Е	0.95	1.05	1.00
е	_	_	0.50
L	0.25	0.35	0.30
Ζ			0.10
Z 1	0.045	0.105	0.075
All Dimensions in mm			



Suggested Pad Layout

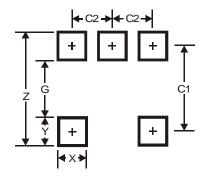
 $\label{please} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

(1) Package Type: SOT25



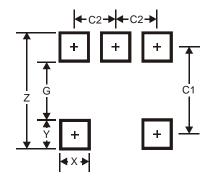
Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

(2) Package Type: SOT353



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Υ	0.6
C1	1.9
C2	0.65

(3) Package Type: SOT553



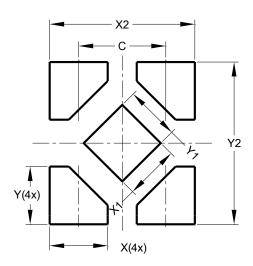
Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



Suggested Pad Layout (Continued)

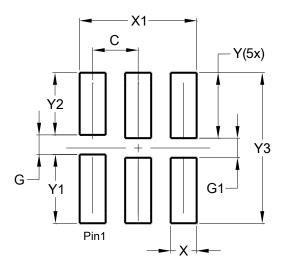
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type X2-DFN0808-4



Dimensions	Value (in mm)
С	0.480
X	0.320
X1	0.300
X2	0.800
Y	0.320
Y1	0.300
Y2	0.900

(5) Package Type X1-DFN1010-6



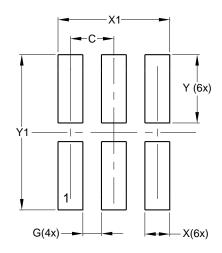
Dimensions	Value (in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Υ	0.500
Y1	0.525
Y2	0.475
Y3	1.150



Suggested Pad Layout (Cont.)

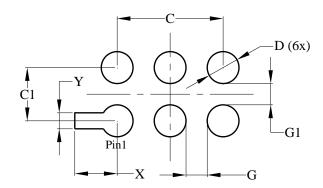
Please see http://www.diodes.com/package-outlines.html for the latest version.

(6) Package Type X2-DFN1010-6



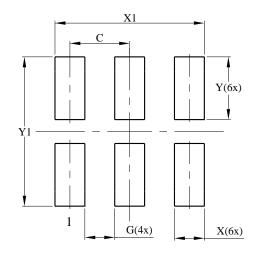
Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

(7) Package Type: X2-DFN1409-6 (Chip Scale Alternative)



Dimensions	Value (in mm)
C	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
x	0.400
Y	0.150

(8) Package Type: X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



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